

CORRECTION

[View Article Online](#)
[View Journal](#) | [View Issue](#)



CrossMark
 click for updates

Cite this: *J. Mater. Chem. A*, 2017, 5, 428

DOI: 10.1039/c6ta90249a

www.rsc.org/MaterialsA

Correction: ZnO nanorods decorated with metal sulfides as stable and efficient counter-electrode materials for high-efficiency quantum dot-sensitized solar cells

Chandu V. V. M. Gopi, Mallineni Venkata-Haritha, Young-Seok Lee and Hee-Je Kim*

Correction for 'ZnO nanorods decorated with metal sulfides as stable and efficient counter-electrode materials for high-efficiency quantum dot-sensitized solar cells' by Chandu V. V. M. Gopi *et al.*, *J. Mater. Chem. A*, 2016, 4, 8161–8171.

There is an error in the film thicknesses of the ZnO/metal sulfides section of the above manuscript. The correct film thicknesses of the ZnO/metal sulfides are described below.

It is well known that the film thickness of FTO layer is 0.62 μm , which is in good agreement with the result obtained in Fig. 1(k). Based on these data, the ZnO/metal sulfide thicknesses were carefully calculated again by subtracting the thickness of FTO from the total FTO/ZnO/metal sulfide thicknesses. Based on this, the real film thicknesses are 1.47 μm for ZnO nanorod, 0.92 μm for ZnO/CoS, 1.30 μm for ZnO/NiS, 0.29 μm for ZnO/CuS, and 0.86 μm for ZnO/PbS, as shown in Fig. 1 below.

School of Electrical Engineering, Pusan National University, Busandaehak-ro 63 beon-gil, Geumjeong-gu, Busan, 46241, South Korea. E-mail: heeje@pusan.ac.kr; Fax: +82 51 513 0212; Tel: +82 51 510 2364



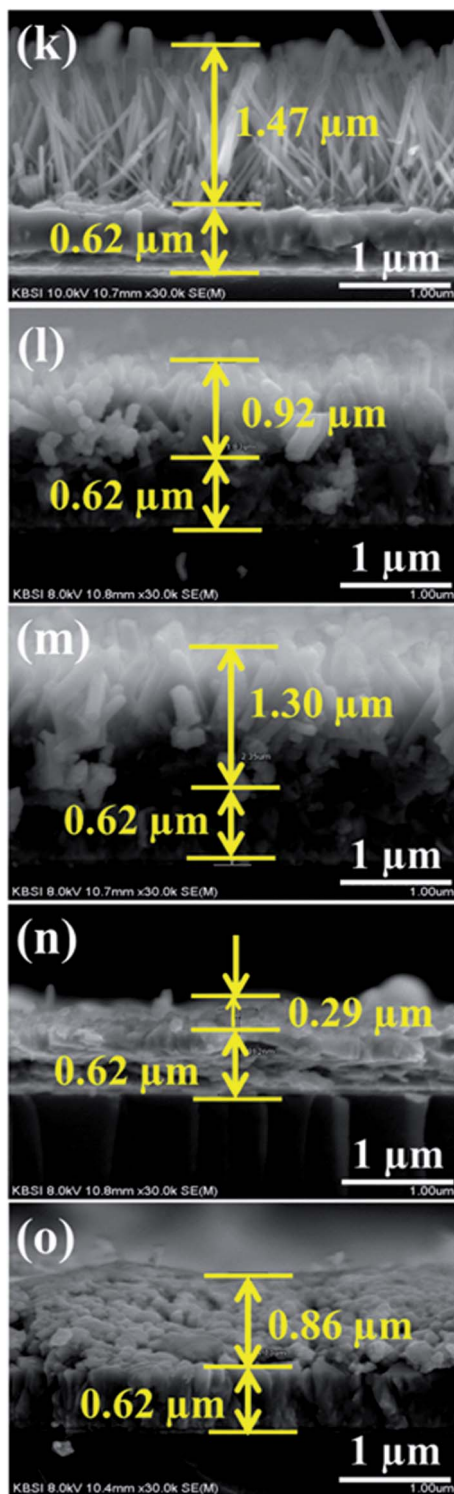


Fig. 1 The film thicknesses for the metal sulfides on ZnO nanorod: (k) ZnO nanorod, (l) ZnO/CoS, (m) ZnO/NiS, (n) ZnO/CuS, and (o) ZnO/PbS.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.